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(54) **Title:** METHOD OF FORMING SILICON CARBIDE EPITAXIAL WAFER AND SILICON CARBIDE SUBSTRATE

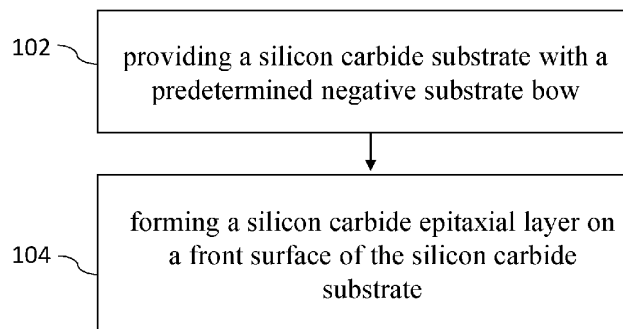


FIG. 1

(57) **Abstract:** Various embodiments may relate to a method of forming a silicon carbide epitaxial wafer. The method may include providing a silicon carbide substrate with a predetermined negative substrate bow, and forming a silicon carbide epitaxial layer on a front surface of the silicon carbide substrate.

WO 2023/101613 A2